

Silicon NPN Power Transistors

BU626A

DESCRIPTION

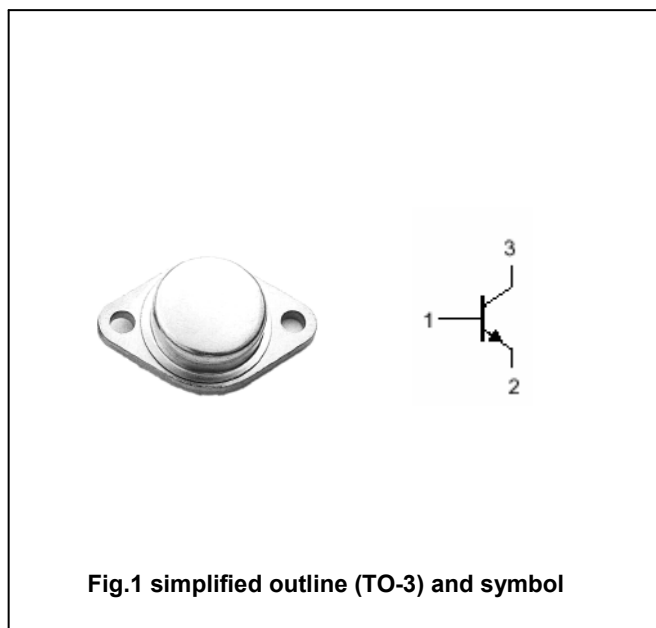
- With TO-3 package
- Short switching times.
- High dielectric strength.

APPLICATIONS

- For use in power supply units of TV receives.

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1000	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		10	A
I_{CM}	Collector current-peak		15	A
P_T	Total power dissipation	$T_C = 25 \square$	100	W
T_j	Junction temperature		175	\square
T_{stg}	Storage temperature		-65~175	\square

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R_{thj-c}	Thermal resistance junction to case	1.5	K/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA; I _B =0;	400			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA; I _C =0;	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =8A; I _B =2.5 A			3.3	V
V _{BEsat}	Base-emitter saturation voltage	I _C =8A; I _B =2.5 A			2.2	V
I _{CES}	Collector cut-off current	V _{CE} =1000V; V _{BE} =0			1.0	mA
h _{FE-1}	DC current gain	I _C =10A ; V _{CE} =1.5V	10			
h _{FE-2}	DC current gain	I _C =2.5A ; V _{CE} =10V	15			
f _T	Transition frequency	I _C =0.1A ; V _{CE} =10V		6		MHz
t _f	Fall time	I _C =8A; I _{B1} =-I _{B2} =2.5A;			1	μs

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PACKAGE OUTLINE

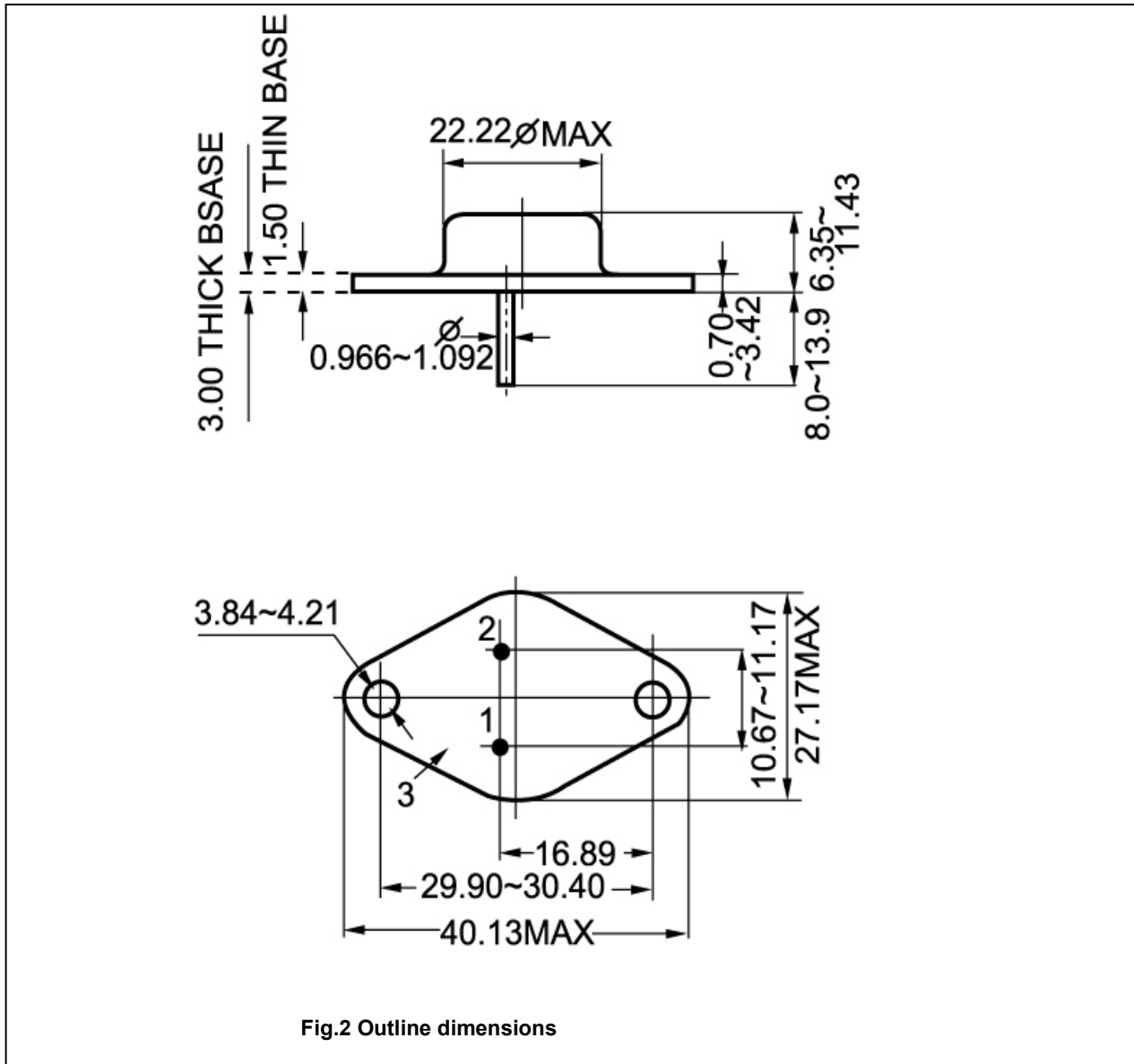


Fig.2 Outline dimensions